

Silicon NPN Power Transistor

2SC5129

DESCRIPTION

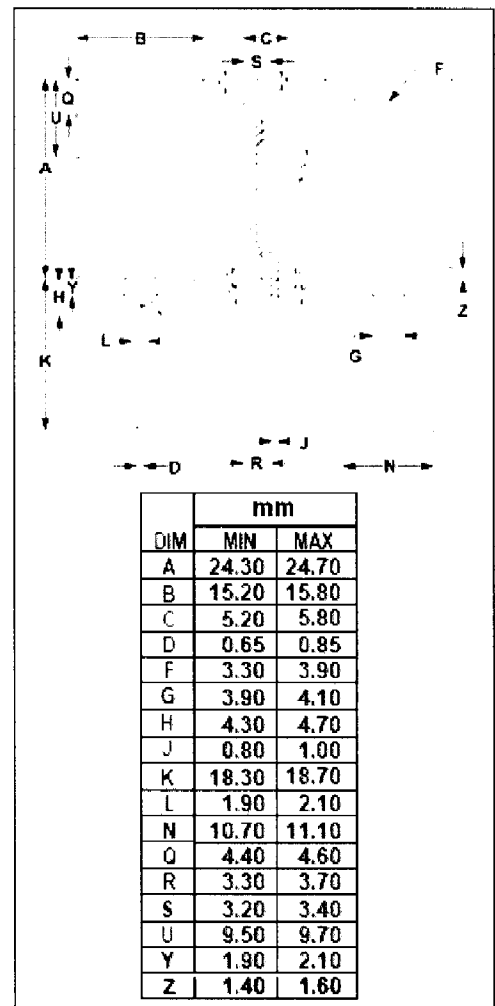
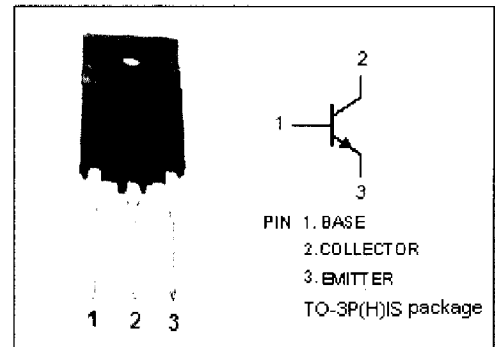
- High Breakdown Voltage-
 : $V_{CBO} = 1500V$ (Min)
- High Switching Speed
- Low Saturation Voltage

APPLICATIONS

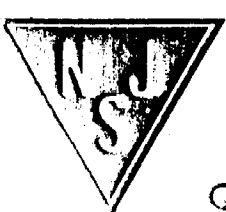
- Horizontal deflection output for high resolution display, color TV.
- High speed switching applications.

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	1500	V
V_{CEO}	Collector-Emitter Voltage	600	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	10	A
I_{CM}	Collector Current-Peak	20	A
I_B	Base Current- Continuous	5	A
P_C	Collector Power Dissipation @ $T_c = 25^\circ C$	50	W
T_J	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$



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ELECTRICAL CHARACTERISTICS

$T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=10\text{mA}; I_B=0$	600			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=6\text{A}; I_B=1.5\text{A}$			3.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=6\text{A}; I_B=1.5\text{A}$			1.4	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=1500\text{V}; I_E=0$			1.0	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$			10	μA
h_{FE-1}	DC Current Gain	$I_C=1\text{A}; V_{CE}=5\text{V}$	10		30	
h_{FE-2}	DC Current Gain	$I_C=6\text{A}; V_{CE}=5\text{V}$	4		8	
f_T	Current-Gain—Bandwidth Product	$I_C=0.1\text{A}; V_{CE}=10\text{V}$		1.7		MHz
C_{OB}	Output Capacitance	$I_E=0; V_{CB}=10\text{V}; f_{\text{test}}=1.0\text{MHz}$		135		pF
t_{stg}	Storage Time	$I_{CP}=5\text{A}; I_{B1(\text{end})}=1\text{A}; f_H=64\text{kHz}$			4.0	μs
t_f	Fall Time				0.3	μs